

Application Data Sheet

Application Information

Application number::	Unassigned
Filing Date::	04/12/2004
Application Type::	Regular
Subject Matter::	Utility
Suggested classification::	
Suggested Group Art Unit::	
CD-ROM or CD-R?::	None
Computer Readable Form (CRF)?::	No
Title::	POROUS SUBSTRATE FOR EPITAXIAL GROWTH, METHOD FOR MANUFACTURING SAME, AND METHOD FOR MANUFACTURING III-NITRIDE SEMICONDUCTOR SUBSTRATE
Attorney Docket Number::	035532-0141
Request for Early Publication?::	No
Request for Non-Publication?::	No
Suggested Drawing Figure::	
Total Drawing Sheets::	5
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

Applicant Information

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Yuichi

Family Name:: OSHIMA
City of Residence:: Tokyo
Country of Residence:: Japan
Street of mailing address:: c/o HITACHI CABLE, LTD.
6-1, Otemachi 1-chome
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Country of mailing address:: Japan

Applicant Authority Type:: Inventor
Primary Citizenship Country:: Japan
Status:: Full Capacity
Given Name:: Masatomo
Family Name:: SHIBATA
City of Residence:: Tokyo
Country of Residence:: Japan
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Country of mailing address:: Japan

Correspondence Information

Correspondence Customer Number:: 22428
E-Mail address:: PTOMailWashington@Foley.com

Representative Information

Representative Customer Number::	22428	
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Domestic Priority Information

Application::	Continuity Type::	Parent Application::	Parent Filing Date::

Foreign Priority Information

Country::	Application number::	Filing Date::	Priority Claimed::
Japan	2003-110726	04/15/2003	Yes

Assignee Information

Assignee name:: HITACHI CABLE, LTD.